

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently amended) A method of manufacturing a semiconductor device comprising the steps of:
  - forming a semiconductor layer on an insulating surface;
  - forming an insulating film on said semiconductor layer;
  - forming a first electrode comprising ~~a lamination of~~ a first conductive layer having a first width on said insulating film and a second conductive layer on said ~~insulating film~~ first conductive layer;
  - forming a high concentration impurity region in said semiconductor layer by adding **[[an]]** a first impurity element using said first electrode as a mask;
  - forming a second electrode comprising ~~a lamination of~~ said first conductive layer having said first width and **[[a]]** said second conductive layer having a second width that is different from said first width by etching said second conductive layer of said first electrode;
  - forming a third electrode comprising ~~a lamination of~~ said first conductive layer having a third width that is different from said first and second widths and said second conductive layer having said second width by etching said first conductive layer of said second electrode; and
  - forming a low concentration impurity region in said semiconductor layer by adding **[[an]]** a second impurity element through at least one of said first conductive layer **[[or]]** and said insulating film using said second conductive layer as a mask.
2. (Original) The method according to claim 1 wherein said second width is narrower than said first width.

3. (Original) The method according to claim 1 wherein said third width is narrower than said first width and is wider than said second width.

4. (Currently amended) The method according to claim 1 wherein, after a first conductive film and a second conductive film are formed in a lamination on said insulating film, said second conductive layer is formed by performing a first etching process with said second conductive film, and said first conductive layer having said first width is formed by performing a second etching process with said first conductive film, whereby said first electrode comprising a ~~lamination of~~ said first conductive layer having said first width and said second conductive layer is formed.

5. (Original) The method according to claim 1 wherein said first conductive layer comprises TaN.

6. (Original) The method according to claim 1 wherein said second conductive layer comprises W.

7. (Original) The method according to claim 1 wherein said impurity element comprises phosphorus.

8. (Original) The method according to claim 1 wherein said semiconductor device is an electro-luminescence display device.

9. (Previously presented) The method according to claim 1 wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display, a car navigation, a personal computer, a player using a recording medium, a mobile computer, an electronic book, and a portable telephone.

10-18. (Canceled)

19. (Currently amended) A method of manufacturing a semiconductor device comprising the steps of:

- forming a semiconductor layer on an insulating surface;
- forming an insulating film on said semiconductor layer;
- forming a first conductive film and a second conductive film in a lamination on said insulating film;
- forming a second conductive layer having a first width by etching said second conductive film;
- forming a high concentration impurity region in said semiconductor layer by adding **[[an]]** a first impurity element through at least one of said first conductive film **[[or]]** and said insulating film using said second conductive layer having said first width as a mask;
- forming a first electrode comprising ~~a lamination of~~ a first conductive layer having a second width that is different from said first width and **[[a]]** said second conductive layer having a third width that is different from said first and second widths by etching said first conductive film;
- forming a second electrode comprising ~~a lamination of~~ said first conductive layer having said second width and **[[a]]** said second conductive layer having a fourth width that is different from said first, second and third widths by etching said second conductive layer of said first electrode;
- forming a third electrode comprising ~~a lamination of~~ said first conductive layer having a fifth width and said second conductive layer having said fourth width by etching said first conductive layer of said second electrode; and
- forming a low concentration impurity region in said semiconductor layer by adding **[[an]]** a second impurity element through at least one of said first conductive layer **[[or]]** and said insulating film using said second conductive layer having said fourth width as a mask.

20. (Original) The method according to claim 19 wherein said second width is narrower than said first width.

21. (Original) The method according to claim 19 wherein said fifth width is narrower than said second width and is wider than said fourth width.

22. (Original) The method according to claim 19 wherein said first conductive layer comprises TaN.

23. (Original) The method according to claim 19 wherein said second conductive layer comprises W.

24. (Original) The method according to claim 19 wherein said impurity element comprises phosphorus.

25. (Original) The method according to claim 19 wherein said semiconductor device is an electro-luminescence display device.

26. (Previously presented) The method according to claim 19 wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display, a car navigation, a personal computer, a player using a recording medium, a mobile computer, an electronic book, and a portable telephone.

27. (Currently amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor layer on an insulating surface;

forming an insulating film on said semiconductor layer;

forming a first conductive film and a second conductive film in a lamination on said

insulating film;

forming a second conductive layer having a first width by etching said second conductive film;

forming a high concentration impurity region in said semiconductor layer by adding **[[an]]** a first impurity element through at least one of said first conductive film **[[or]]** and said insulating film using said second conductive layer having said first width as a mask;

forming **[[a]]** said second conductive layer having a second width that is different from said first width by etching said second conductive layer;

forming an electrode comprising ~~a lamination of~~ a first conductive layer having a third width that is different from said first and second widths and said second conductive layer having said second width by etching said first conductive film; and

forming a low concentration impurity region in said semiconductor layer by adding **[[an]]** a second impurity element through at least one of said first conductive layer **[[or]]** and said insulating film using said second conductive layer having said second width as a mask.

28. (Original) The method according to claim 27 wherein said second width is narrower than said first width.

29. (Original) The method according to claim 27 wherein said third width is narrower than said first width and is wider than said second width.

30. (Original) The method according to claim 27 wherein said first conductive layer comprises TaN.

31. (Original) The method according to claim 27 wherein said second conductive layer comprises W.

32. (Original) The method according to claim 27 wherein said impurity element comprises phosphorus.

33. (Original) The method according to claim 27 wherein said semiconductor device is an electro-luminescence display device.

34. (Previously presented) The method according to claim 27 wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display, a car navigation, a personal computer, a player using a recording medium, a mobile computer, an electronic book, and a portable telephone.

35. (Currently amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor layer on an insulating surface;

forming an insulating film on said semiconductor layer;

forming a first conductive film and a second conductive film in a lamination on said insulating film;

forming a second conductive layer having a first width by etching said second conductive film;

forming a high concentration impurity region in said semiconductor layer by adding **[[an]]** a first impurity element through at least one of said first conductive film **[[or]]** and said insulating film using said second conductive layer having said first width as a mask;

forming an electrode comprising ~~a lamination of~~ a first conductive layer having a second width that is different from said first width and **[[a]]** said second conductive layer having a third width that is different from said first and second widths by etching said first conductive film and said second conductive layer; and

forming a low concentration impurity region in said semiconductor layer by adding **[[an]]** a second impurity element through at least one of said first conductive layer **[[or]]** and said

insulating film using said second conductive layer having said third width as a mask.

36. (Original) The method according to claim 35 wherein said third width is narrower than said first width.

37. (Original) The method according to claim 35 wherein said second width is narrower than said first width and is wider than said third width.

38. (Original) The method according to claim 35 wherein said first conductive layer comprises TaN.

39. (Original) The method according to claim 35 wherein said second conductive layer comprises W.

40. (Original) The method according to claim 35 wherein said impurity element comprises phosphorus.

41. (Original) The method according to claim 35 wherein said semiconductor device is an electro-luminescence display device.

42. (Previously presented) The method according to claim 35 wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display, a car navigation, a personal computer, a player using a recording medium, a mobile computer, an electronic book, and a portable telephone.